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February 2016

# FGA40S65SH

## 650 V, 40 A Field Stop Trench IGBT

### Features

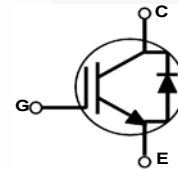
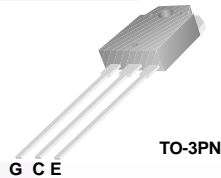
- Maximum Junction Temperature :  $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.4 \text{ V (Typ.) @ } I_C = 40 \text{ A}$
- 100% of the Parts tested for  $I_{LM}(1)$
- High Input Impedance
- Tighten Parameter Distribution
- RoHS Compliant

### General Description

Using Fairchild's proprietary trench design and advanced field stop IGBT technology, 650V field stop offers superior conduction and switching performance and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating and MWO.

### Applications

- Induction Heating, MWO



### Absolute Maximum Ratings

Symbol	Description	FGA40S65SH	Unit
$V_{CES}$	Collector to Emitter Voltage	650	V
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V
	Transient Gate to Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current @ $T_C = 25^{\circ}\text{C}$	80	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	40	A
$I_{LM}(1)$	Pulsed Collector Current @ $T_C = 25^{\circ}\text{C}$	120	A
$I_{CM}(2)$	Pulsed Collector Current	120	A
$I_F$	Diode Forward Current @ $T_C = 25^{\circ}\text{C}$	40	A
	Diode Forward Current @ $T_C = 100^{\circ}\text{C}$	20	A
$I_{FM}$	Pulsed Diode Maximum Forward Current	240	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$	268	W
	Maximum Power Dissipation @ $T_C = 100^{\circ}\text{C}$	134	W
$T_J$	Operating Junction Temperature	-55 to +175	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^{\circ}\text{C}$

### Thermal Characteristics

Symbol	Parameter	FGA40S65SH	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	0.56	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	$^{\circ}\text{C}/\text{W}$

**Notes:**

1.  $V_{OC} = 400 \text{ V}$ ,  $V_{GE} = 15 \text{ V}$ ,  $I_C = 120 \text{ A}$ ,  $R_G = 35 \Omega$ , Inductive Load
2. Repetitive rating: Pulse width limited by max. junction temperature

FGA40S65SH — 650 V, 40 A Field Stop Trench IGBT

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Qty per Tube
FGA40S65SH	FGA40S65SH	TO-3PN	-	-	30

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	-	0.65	-	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	μA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	± 400	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 40\text{ mA}, V_{CE} = V_{GE}$	4.0	5.3	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	1.40	1.81	V
		$I_C = 40\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$	-	1.65	-	V
$V_{FM}$	Diode Forward Voltage	$I_F = 20\text{ A}, T_C = 25^\circ\text{C}$	-	1.45	1.95	V
		$I_F = 20\text{ A}, T_C = 175^\circ\text{C}$	-	1.65	-	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	-	2012	-	pF
$C_{oes}$	Output Capacitance		-	49	-	pF
$C_{res}$	Reverse Transfer Capacitance		-	26	-	pF
<b>Switching Characteristics</b>						
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 40\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V}, \text{Resistive Load}, T_C = 25^\circ\text{C}$	-	19.2	-	ns
$T_r$	Rise Time		-	65.6	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	68.8	-	ns
$T_f$	Fall Time		-	96.8	-	ns
$E_{on}$	Turn-On Switching Loss		-	194	-	μJ
$E_{off}$	Turn-Off Switching Loss		-	388	-	μJ
$E_{ts}$	Total Switching Loss		-	592	-	μJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 40\text{ A}, R_G = 6\ \Omega, V_{GE} = 15\text{ V}, \text{Resistive Load}, T_C = 175^\circ\text{C}$	-	19.2	-	ns
$T_r$	Rise Time		-	87.2	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	75.2	-	ns
$T_f$	Fall Time		-	158	-	ns
$E_{on}$	Turn-On Switching Loss		-	292	-	μJ
$E_{off}$	Turn-Off Switching Loss		-	633	-	μJ
$E_{ts}$	Total Switching Loss		-	925	-	μJ
$Q_g$	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	-	73	-	nC
$Q_{ge}$	Gate to Emitter Charge		-	13	-	nC
$Q_{gc}$	Gate to Collector Charge		-	28	-	nC

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

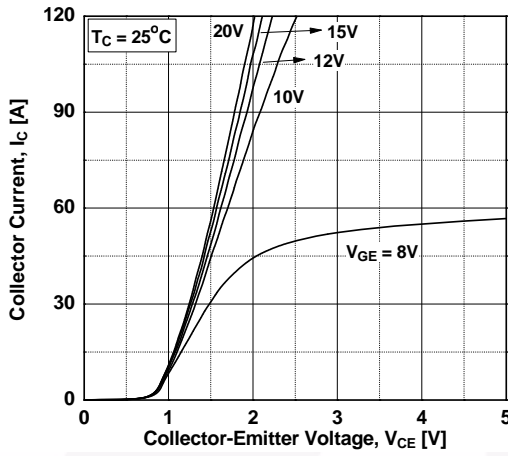


Figure 2. Typical Output Characteristics

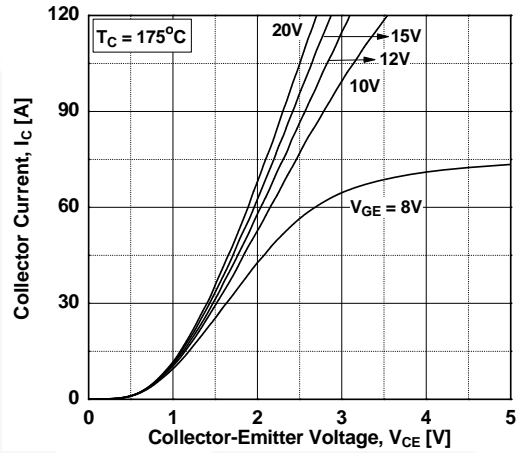


Figure 3. Typical Saturation Voltage Characteristics

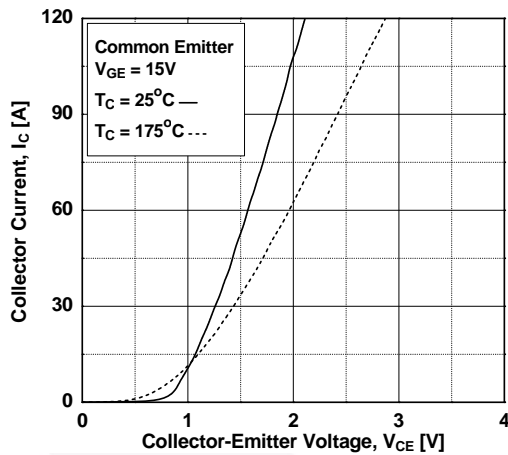


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

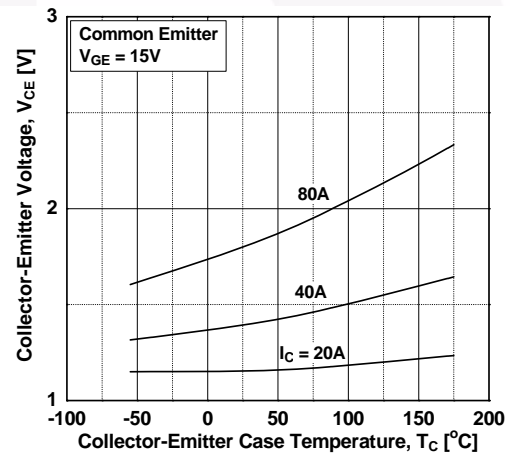


Figure 5. Saturation Voltage vs.  $V_{GE}$

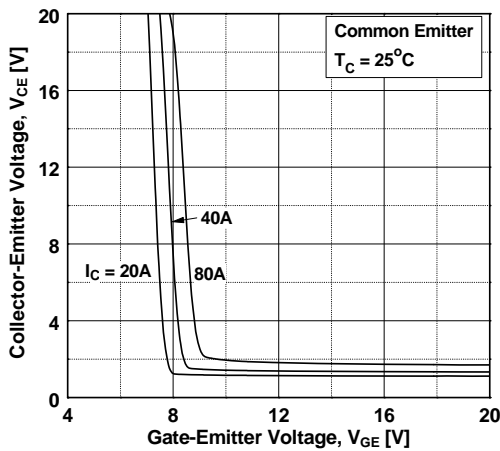
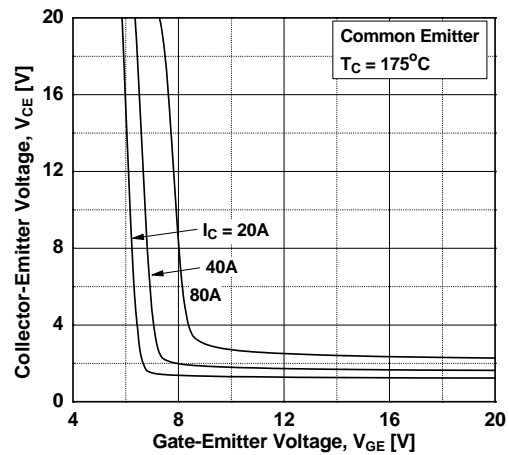


Figure 6. Saturation Voltage vs.  $V_{GE}$



## Typical Performance Characteristics

Figure 7. Capacitance Characteristics

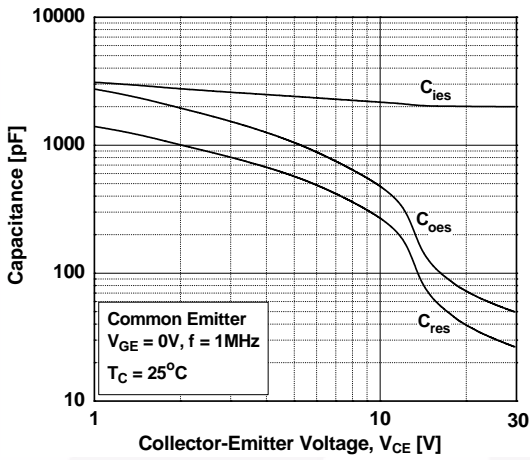


Figure 8. Gate charge Characteristics

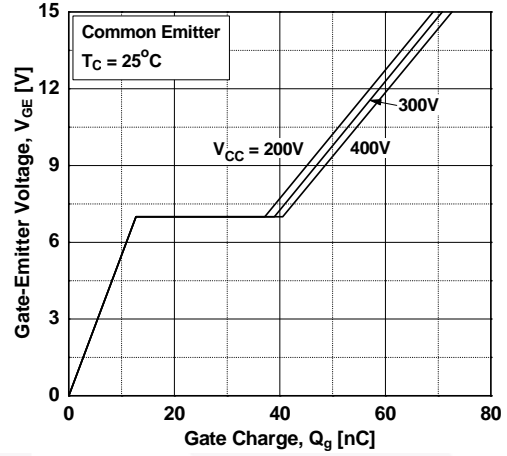


Figure 9. Turn-on Characteristics vs. Gate Resistance

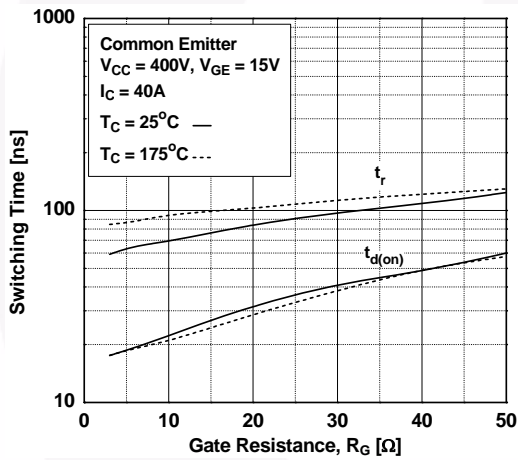


Figure 10. Turn-off Characteristics vs. Gate Resistance

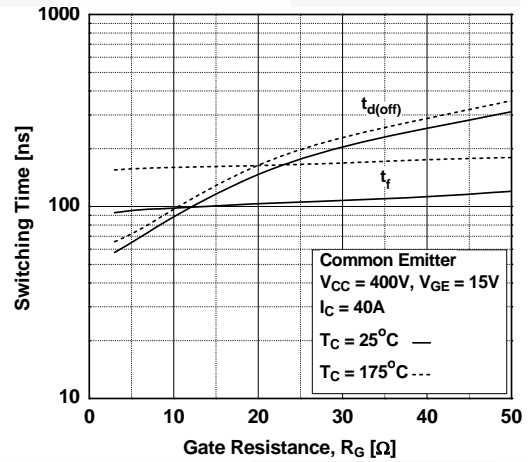


Figure 11. Switching Loss vs. Gate Resistance

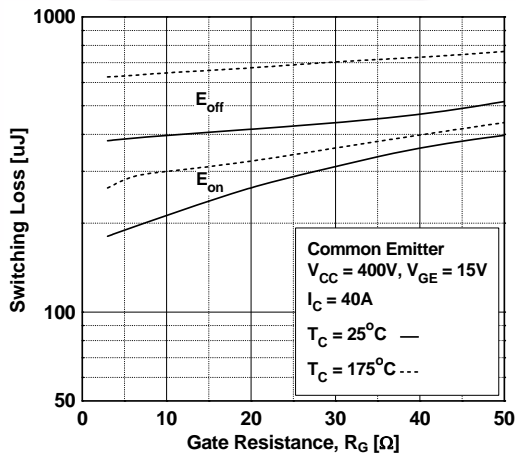
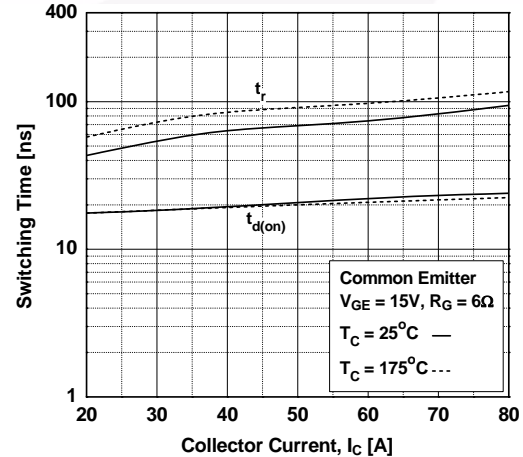


Figure 12. Turn-on Characteristics vs. Collector Current



## Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

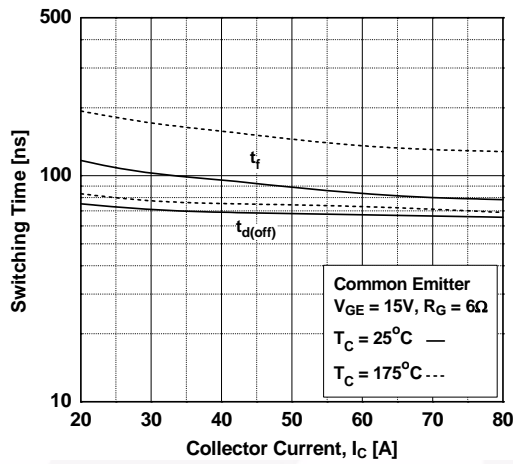


Figure 14. Switching Loss vs. Collector Current

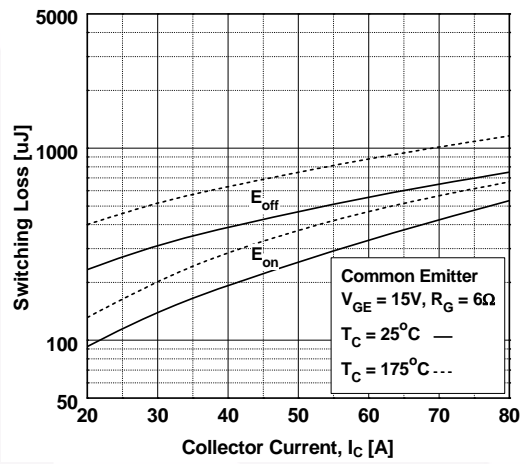


Figure 15. Load Current Vs. Frequency

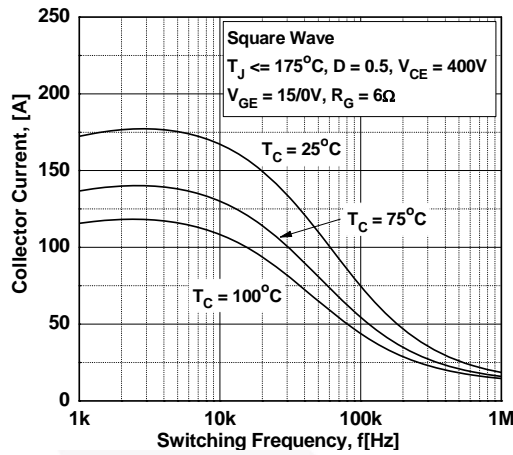


Figure 16. SOA Characteristics

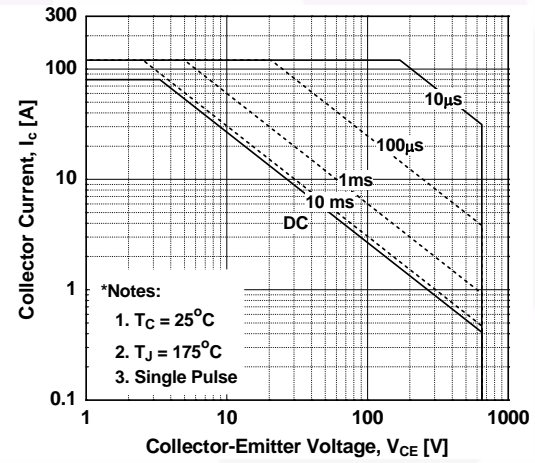
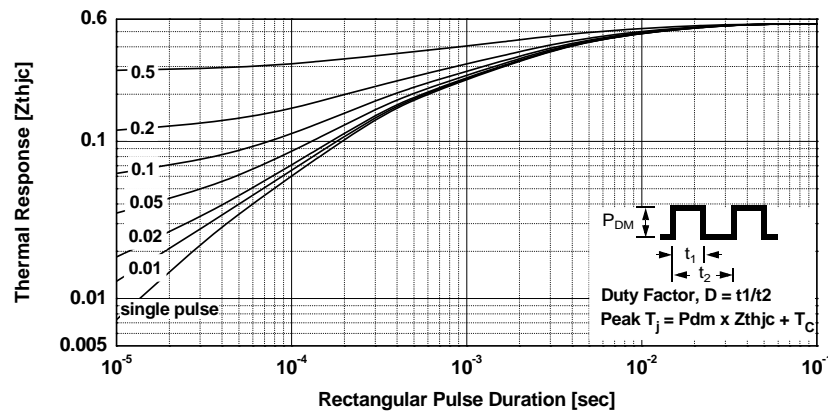
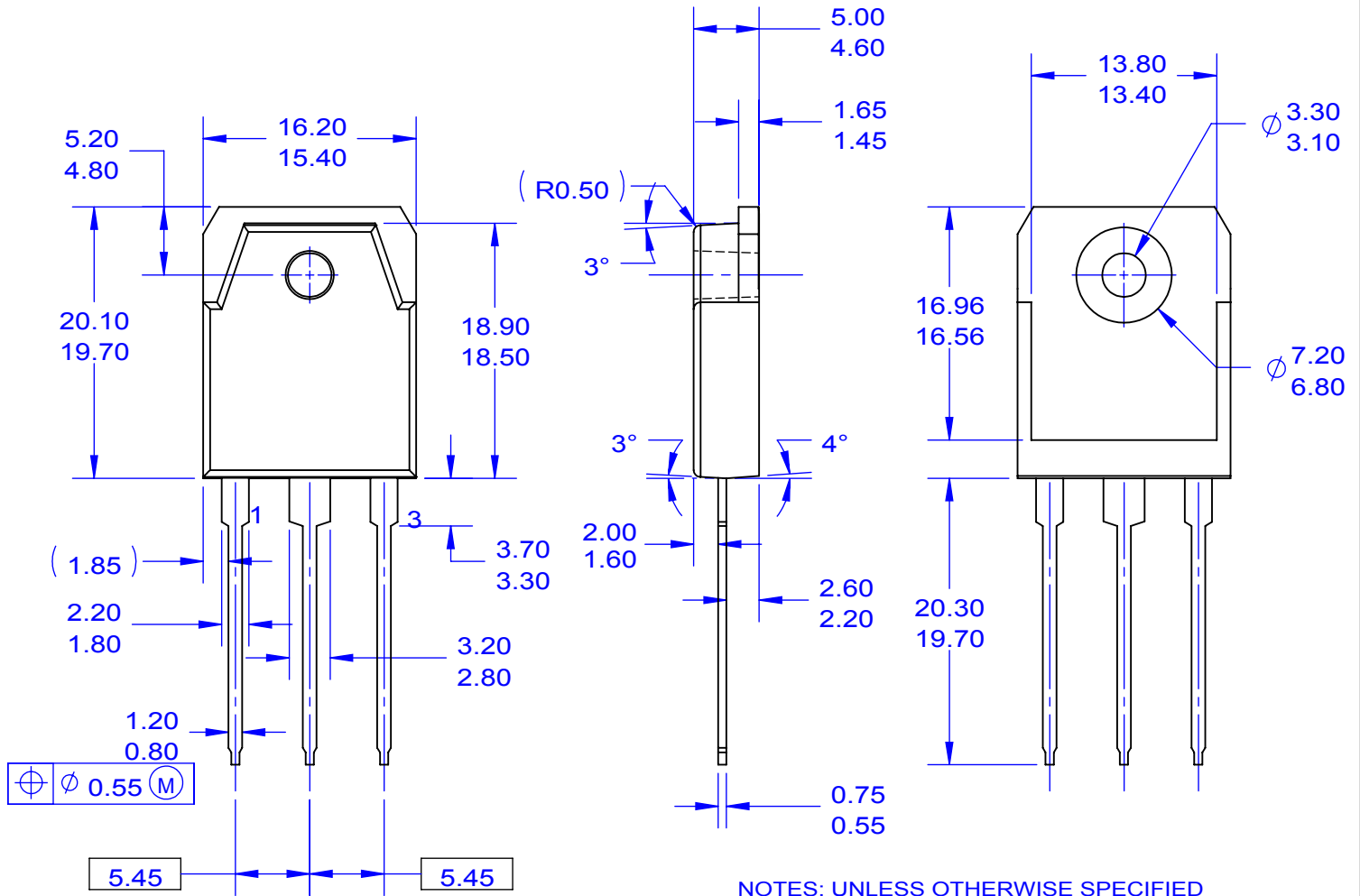


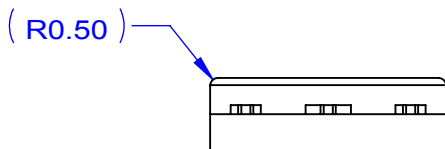
Figure 17. Transient Thermal Impedance of IGBT





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